



FZT951

60V PNP MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > -60V
- I_C = -5A High Continuous Collector Current
- I_{CM} = -15A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < -140mV @ -1A
- $R_{CE(SAT)} = 55m\Omega$ for a Low Equivalent On-Resistance
- h_{FE} Specified up to -10A for a High Gain Hold-Up
- Complementary NPN Type: FZT851
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

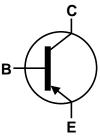
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

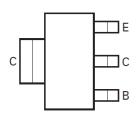
SOT223



Top View



Device Symbol



Top View Pin-Out

Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT951TA	AEC-Q101	FZT951	7	12	1000
FZT951TC	AEC-Q101	FZT951	13	12	4000
FZT951QTA	Automotive	FZT951	7	12	1000
FZT951QTC	Automotive	FZT951	13	12	4000

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

SOT223

FZT
951

951

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FZT 951 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 8 = 2018) WW or $\overline{W}W$ = Week Code (01–53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-5	Α
Peak Pulse Current	I _{CM}	-15	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)		3.0 24	W	
Linear Derating Factor	(Note 7)	P _D	1.6 12.8	mW /°C	
Thermal Decistores Junction to Ambient	(Note 6)	R _{ÐJA}	42		
Thermal Resistance, Junction to Ambient	(Note 7)	R _{ÐJA}	78	°C/W	
Thermal Resistance Junction to Lead (Note 8)		R _{OJL}	8.8		
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C		

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	8000	V	3B
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

Notes:

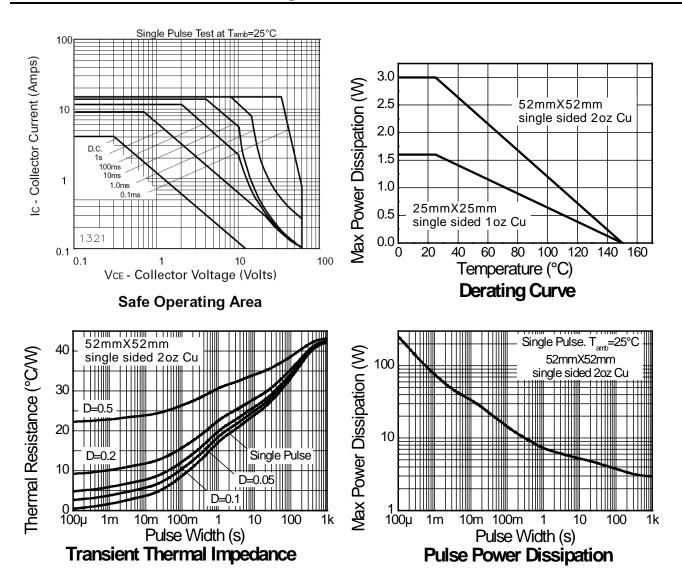
- 6. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 7. Same as Note 6, except the device is mounted on 25mm × 25mm 1oz copper.

 8. Thermal resistance from junction to solder-point (at the end of the collector lead).

 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

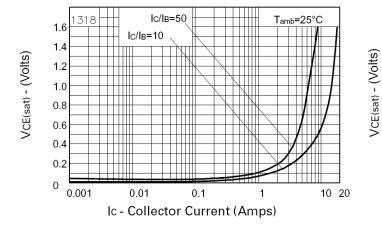
Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-100	-140	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CER}	-100	-140	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-60	-90	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8	_	V	$I_E = -100 \mu A$
Collector Cut-Off Current	I _{CBO}	_	<-1 —	-50 -1	nΑ μΑ	V _{CB} = -80V V _{CB} = -80V, T _A = +100°C
Collector Cut-Off Current	I _{CER}	_	<-1 —	-50 -1	nΑ μΑ	$V_{CE} = -80V, R \le 1k\Omega$ $V_{CE} = -80V, T_{A} = +100^{\circ}C$
Emitter Cut-Off Current	I _{EBO}		<1	-10	nA	V _{EB} = -6V
		100	200	_	_	I _C = -10mA, V _{CE} = -1V
DC Current Transfer Static Patic (Note 10)	L	100	200	300		I _C = -2A, V _{CE} = -1V
DC Current Transfer Static Ratio (Note 10)	h _{FE}	75	90	_		$I_C = -5A$, $V_{CE} = -1V$
		10	25	_		I _C = -10A, V _{CE} = -1V
	Vce(sat)	_	-20	-50	mV	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
Collector-Emitter Saturation Voltage (Note 10)		_	-85	-140		$I_C = -1A$, $I_B = -100mA$
Collector-Emilier Saturation Voltage (Note 10)		_	-155	-210		$I_C = -2A$, $I_B = -200mA$
		I	-370	-460		$I_C = -5A$, $I_B = -500mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(SAT)}		-1080	-1240	mV	$I_C = -5A$, $I_B = -500mA$
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(ON)}$	1	-935	-1070	mV	$I_C = -5A$, $V_{CE} = -1V$
Transitional Frequency (Note 10)	f_{T}	_	120	_	MHz	$I_C = -100 \text{mA}, V_{CE} = -10 \text{V},$ f = 50MHz
Output Capacitance	С _{ОВО}	I	74	_	pF	V _{CB} = -10V, f = 1MHz
Switching Time	ton	_	82	_	20	V _{CC} = -10V, I _C = -2A,
Switching Time	t _{OFF}		350	_	ns	$-I_{B1} = I_{B2} = -200 \text{mA}$

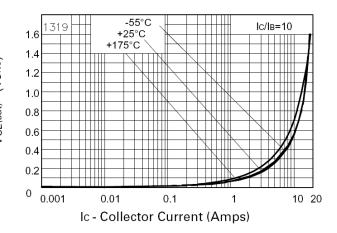
Note:

10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

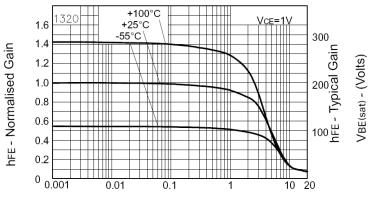


Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



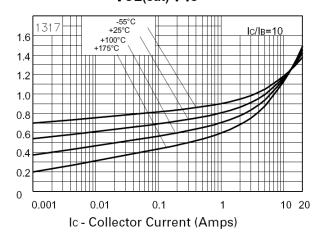


VCE(sat) v IC



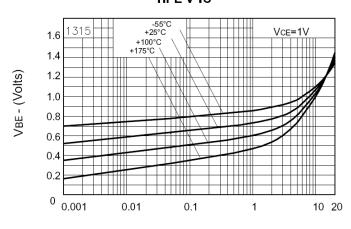
Ic - Collector Current (Amps)

VCE(sat) v IC



VBE(sat) v IC

hfe v lc



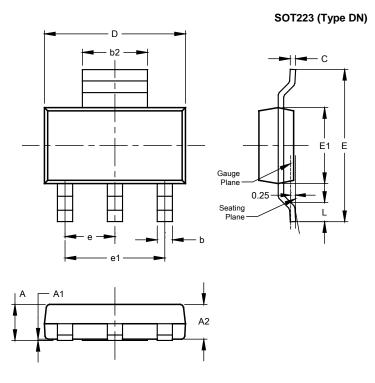
Ic - Collector Current (Amps)

VBE(on) v IC



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

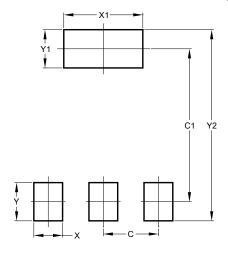


SOT222 (Type DN)					
SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10	-		
С	0.20	0.32			
D	6.30	6.70	-		
Е	6.70	7.30			
E1	3.30	3.70			
е			2.30		
e1			4.60		
Ĺ	0.85				
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
X	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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